



PSMN041-100MSE

N-channel 100 V, 42 mOhm standard level ASFET with enhanced SOA in LFAK33 package. Recommended for fault tolerant applications including high power PoE, inrush management, eFuse and relay replacement

2 October 2023

Objective data sheet

1. General description

New standards and proprietary approaches are enabling Power-over-Ethernet (PoE) systems capable of delivering up to 90 W to each powered device (PD). Such solutions place increased demands on the power sourcing equipment (PSE) in terms of “soft-start”, thermal management and power density requirements. These ASFETs combine enhanced SOA in a compact 3.3 mm x 3.3 mm footprint making them ideally placed for a variety of applications including HP-PoE, eFuse and relay replacement.

2. Features and benefits

- Enhanced safe operating area (SOA) for superior linear mode operation
- Low R_{DSon} for low I^2R losses
- Ultra reliable LFAK33 package for superior thermal and ruggedness performance
- Very low I_{DSS} leakage

3. Applications

- High power PoE applications (>50 W)
- IEEE802.3at and proprietary solutions
- Fault tolerant load switch - inrush management and eFuse applications
- Battery management applications
- Relay replacement
- WIFI hotspots
- 5G picocells
- CCTV

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	100	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$	-	-	25	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}; \text{Fig. 1}$	-	-	59	W
T_j	junction temperature		-55	-	175	°C
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 5\text{ A}; T_j = 25\text{ °C}$	-	32	42	mΩ
		$V_{GS} = 10\text{ V}; I_D = 5\text{ A}; T_j = 100\text{ °C}$	-	50	67	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$I_D = 25\text{ A}; V_{DS} = 50\text{ V}; V_{GS} = 10\text{ V}; T_j = 25\text{ °C}$	[tbd]	2	[tbd]	nC
$Q_{G(tot)}$	total gate charge		[tbd]	10.5	[tbd]	nC

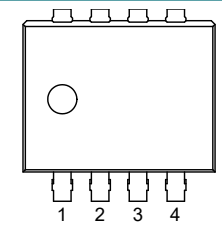
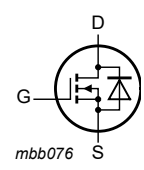
N-channel 100 V, 42 mOhm standard level ASFET with enhanced SOA in LFPAK33 package.
Recommended for fault tolerant applications including high power PoE, inrush management, eFuse and

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
Avalanche ruggedness							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 13\text{ A}$; $V_{sup} \leq 100\text{ V}$; $R_{GS} = 50\ \Omega$; $V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; unclamped; $t_p = 22\text{ s}$	[1]	-	-	18.5	mJ
Source-drain diode							
Q_r	recovered charge	$I_S = 25\text{ A}$; $di_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 50\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 5	-	22	-	nC	

[1] Protected by 100% test

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LFPAK33 (SOT1210)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
PSMN041-100MSE	LFPAK33	Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch	SOT1210

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN041-100MSE	41ES10

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$25\text{ }^\circ\text{C} \leq T_j \leq 175\text{ }^\circ\text{C}$	-	100	V
V_{DGR}	drain-gate voltage	$25\text{ }^\circ\text{C} \leq T_j \leq 175\text{ }^\circ\text{C}$; $R_{GS} = 20\text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-20	20	V
P_{tot}	total power dissipation	$T_{mb} = 25\text{ }^\circ\text{C}$; Fig. 1	-	59	W
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ }^\circ\text{C}$	-	25	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ }^\circ\text{C}$	-	18	A

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Symbol	Parameter	Conditions	Min	Max	Unit
I_{DM}	peak drain current	pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25 \text{ }^\circ\text{C}$; Fig. 2	-	100	A
T_{stg}	storage temperature		-55	175	$^\circ\text{C}$
T_j	junction temperature		-55	175	$^\circ\text{C}$
$T_{sld(M)}$	peak soldering temperature		-	260	$^\circ\text{C}$
Source-drain diode					
I_S	source current	$T_{mb} = 25 \text{ }^\circ\text{C}$	-	25	A
I_{SM}	peak source current	pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25 \text{ }^\circ\text{C}$	-	100	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 13 \text{ A}$; $V_{sup} \leq 100 \text{ V}$; $R_{GS} = 50 \Omega$; $V_{GS} = 10 \text{ V}$; $T_{j(init)} = 25 \text{ }^\circ\text{C}$; unclamped; $t_p = 22 \text{ s}$	[1]	-	18.5 mJ
I_{AS}	non-repetitive avalanche current	$V_{sup} = 100 \text{ V}$; $V_{GS} = 10 \text{ V}$; $T_{j(init)} = 25 \text{ }^\circ\text{C}$; $R_{GS} = 50 \Omega$	[1]	-	13 A

[1] Protected by 100% test

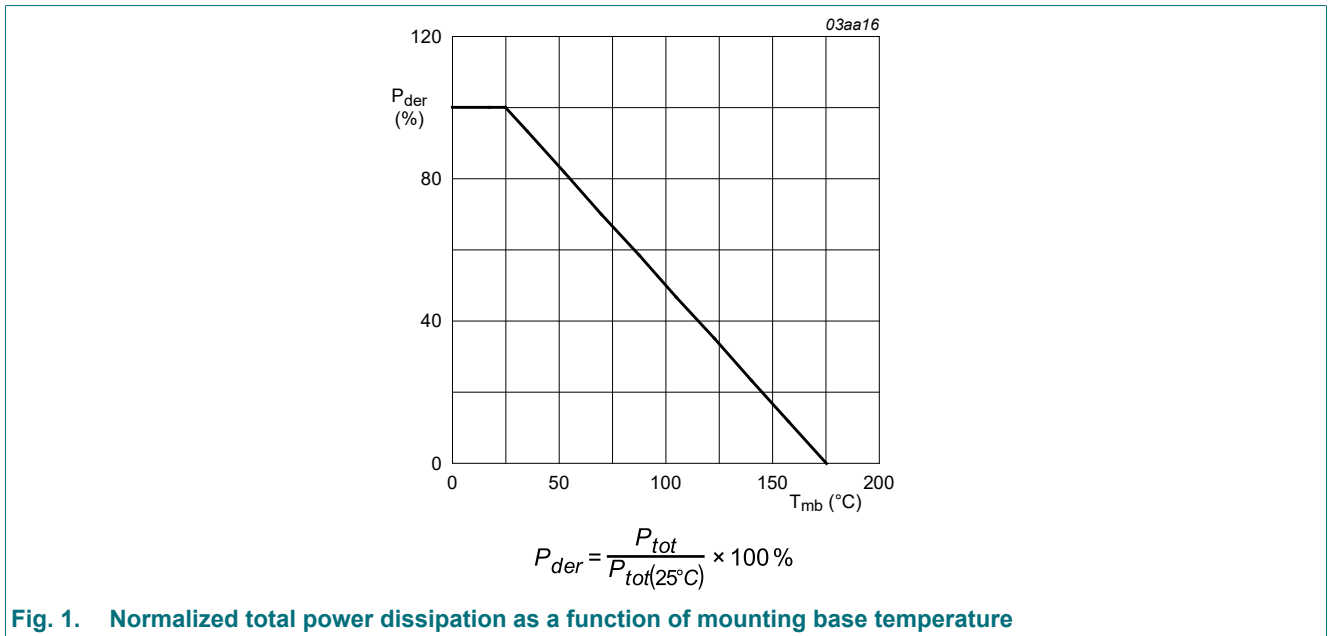
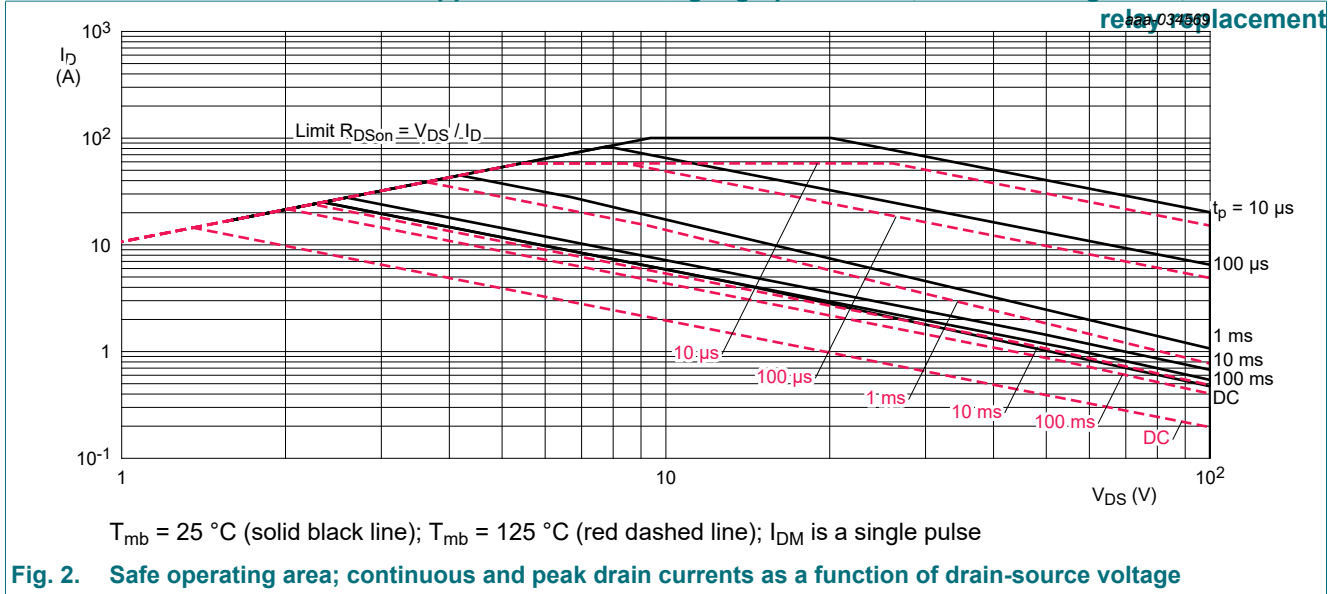


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

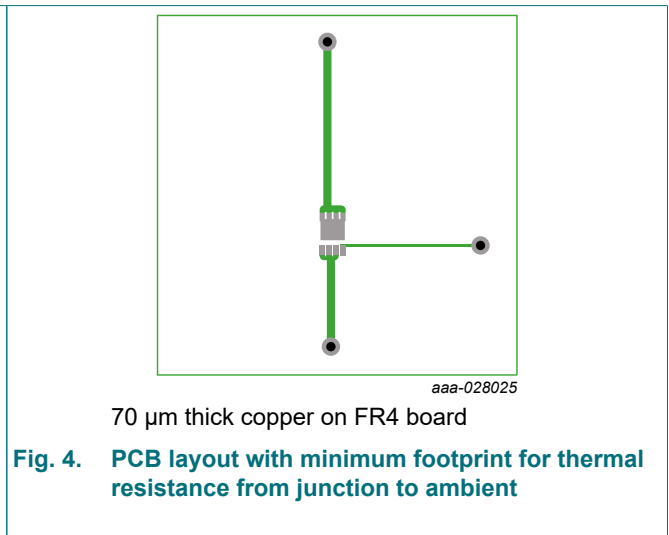
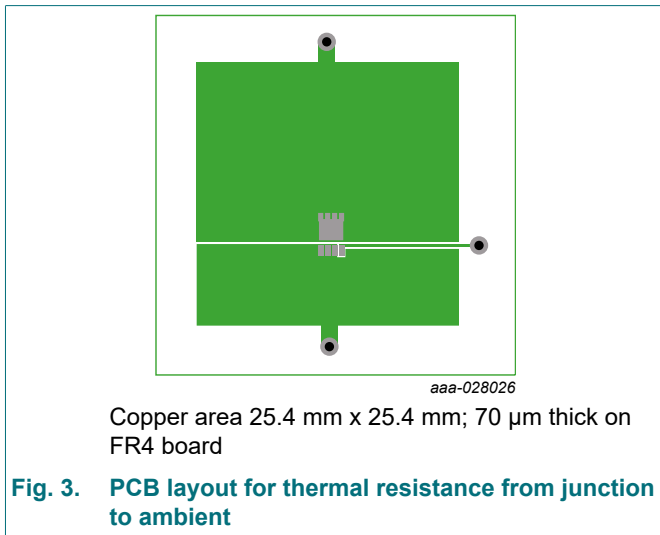
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	2.33	2.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 3	-	50	-	K/W
		Fig. 4	-	130	-	K/W



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	100	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ }^\circ C$	2	2.8	3.6	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ }^\circ C$	-	[tbd]	-	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = -55 \text{ }^\circ C$	-	[tbd]	-	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25 \text{ }^\circ C \leq T_j \leq 150 \text{ }^\circ C$	-	[tbd]	-	mV/K
I_{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	0.003	-	1	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$	-	-	100	μA
I_{GSS}	gate leakage current	$V_{DS} = 20 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{DS} = -20 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ }^\circ C$	-	32	42	m Ω
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 100 \text{ }^\circ C$	-	50	67	m Ω
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 175 \text{ }^\circ C$	-	72	95	m Ω
R_G	gate resistance	$f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$	[tbd]	1.3	[tbd]	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ }^\circ C$	[tbd]	10.5	[tbd]	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	4.6	-	nC
Q_{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ }^\circ C$	[tbd]	4.5	[tbd]	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	2.2	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	2.3	-	nC
Q_{GD}	gate-drain charge		[tbd]	2	[tbd]	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; T_j = 25 \text{ }^\circ C$	-	[tbd]	-	V
C_{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$	[tbd]	612	[tbd]	pF
C_{oss}	output capacitance		[tbd]	134	[tbd]	pF
C_{rss}	reverse transfer capacitance		[tbd]	4.2	[tbd]	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 2 \text{ }^\circ \Omega; V_{GS} = 10 \text{ V}; R_{G(ext)} = 5 \text{ }^\circ \Omega; T_j = 25 \text{ }^\circ C$	-	2.2	-	ns
t_r	rise time		-	1.9	-	ns
$t_{d(off)}$	turn-off delay time		-	5.3	-	ns
t_f	fall time		-	2.7	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	1	V
t_{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A}/\mu s; V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; \text{Fig. 5}$	-	31	-	ns
Q_r	recovered charge	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A}/\mu s; V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; T_j = 25 \text{ }^\circ C; \text{Fig. 5}$	-	22	-	nC

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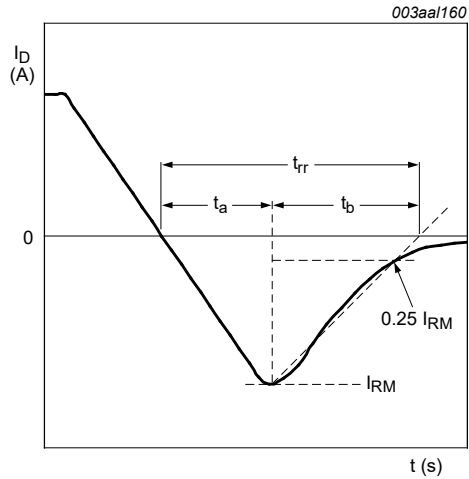


Fig. 5. Reverse recovery timing definition

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11. Package outline

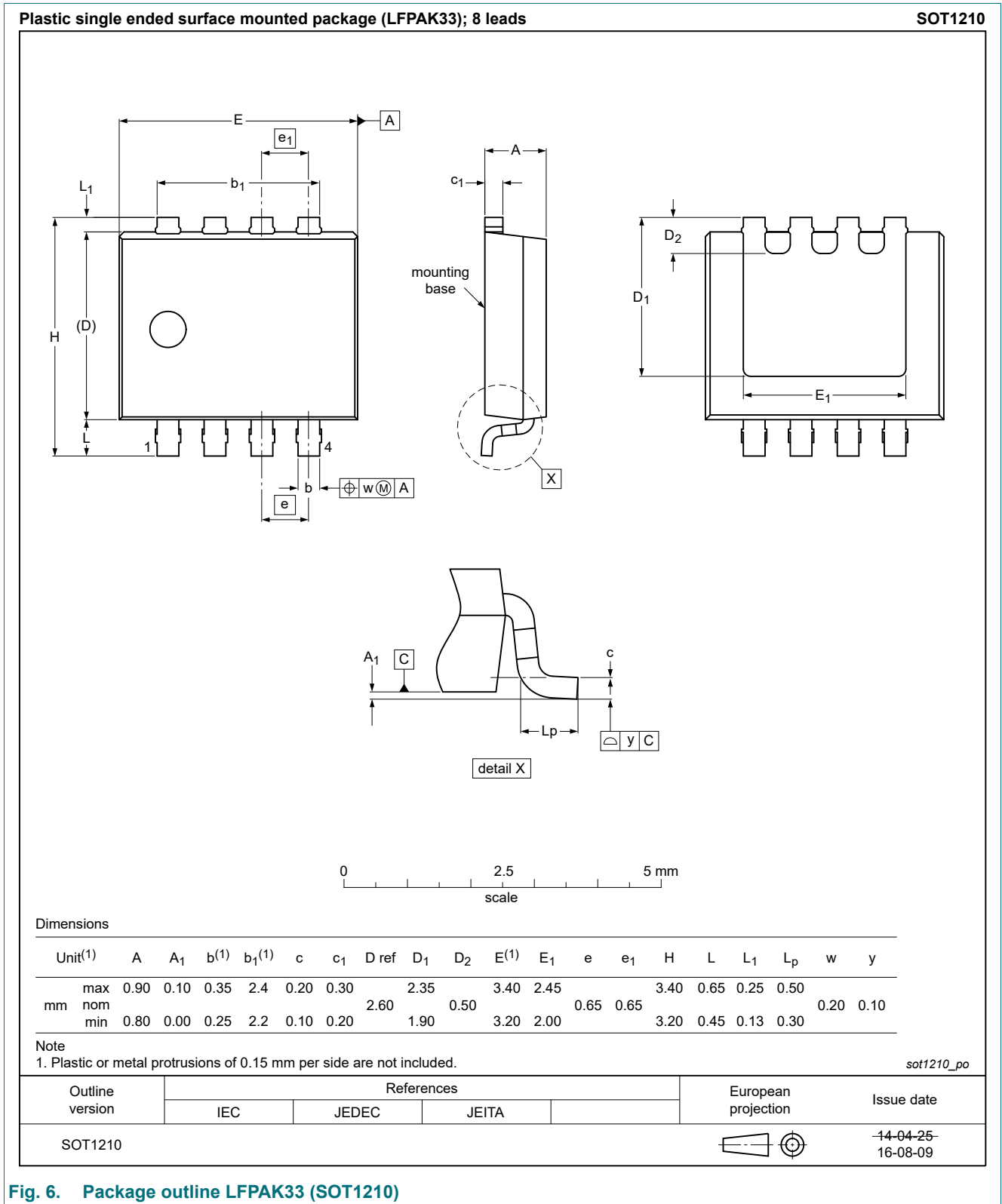
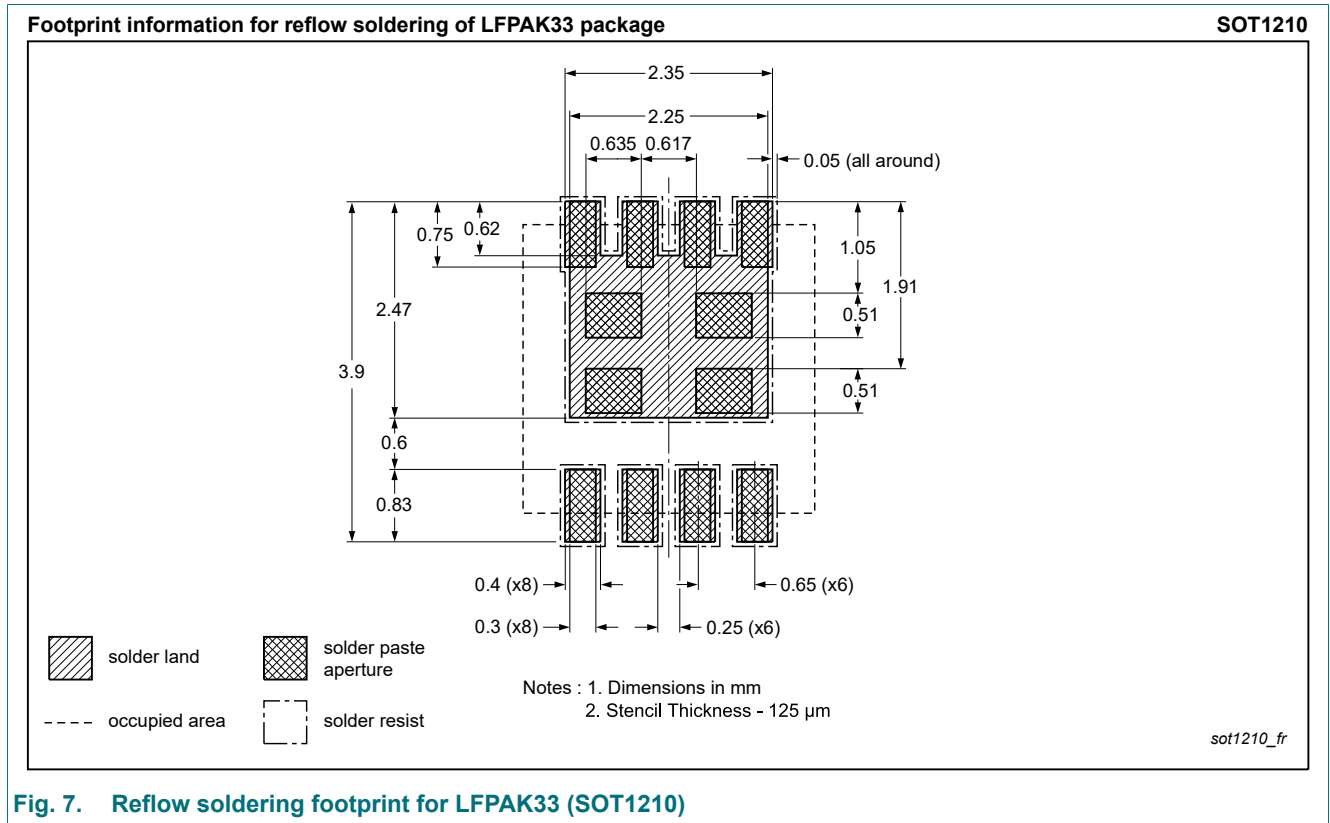


Fig. 6. Package outline LPAK33 (SOT1210)

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12. Soldering



N-channel 100 V, 42 mOhm standard level ASFET with enhanced SOA in LFPK33 package. Recommended for fault tolerant applications including high power PoE, inrush management, eFuse and

13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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